

LEGM35BE120L4HZ

IGBT Power Module

Features:

- $V_{CE}=1200V$ $I_C=35A$
- Low $V_{CE(sat)}$
- V_{CEsat} with positive temperature coefficient
- Maximum junction temperature 150°C
- Isolation Type Package

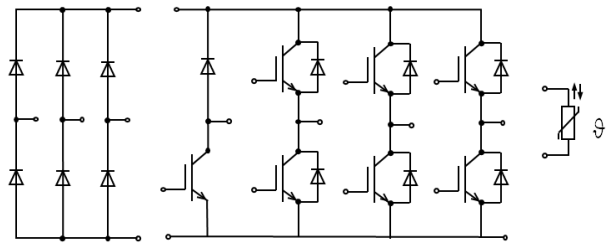
Applications:

- The inverter
- Motor control and drives

Package Type & Internal Circuit



L4



Internal Circuit

Maximum Rated Values (IGBT, Inverter)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	$V_{EC}=0V, I_C=1mA, T_{vj}=25^\circ C$	1200	V
I_C	Continuous Collector Current	$T_C=80^\circ C, T_{vjmax}=150^\circ C$	35	A
I_{CRM}	Peak Collector Current	$I_{CRM}=2I_C$	70	A
V_{GES}	Gate-Emitter Voltage	$T_{vj}=25^\circ C$	± 30	V
P_{tot}	Total Power Dissipation	$T_C=25^\circ C, T_{vjmax}=150^\circ C$	200	W

Characteristics Values (IGBT Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=35\text{ A}, V_{GE}=15\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$		1.83	2.5	V		
		$I_C=35\text{ A}, V_{GE}=15\text{ V}, T_{vj}=125\text{ }^\circ\text{C}$		2.13	2.7	V		
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=2\text{ mA}, V_{CE}=V_{GE}, T_{vj}=25\text{ }^\circ\text{C}$	5.2	6.2	7.0	V		
C_{ies}	Input capacitance	$f=1\text{ MHz}, T_{vj}=25\text{ }^\circ\text{C},$ $V_{CE}=25\text{ V}, V_{GE}=0\text{ V}$			3.11	nF		
C_{res}	Reverse transfer capacitance				103	pF		
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE}=1200\text{ V}, V_{GE}=0\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$			1.2	mA		
I_{GES}	Gate-Emitter Leakage Current	$V_{CE}=0\text{ V}, V_{GE}=20\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$			410	nA		
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	$I_C=35\text{ A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_G=15\Omega$ $T_{vj}=25\text{ }^\circ\text{C}$		50		ns		
t_r	Rise Time, Inductive Load			48		ns		
$t_{d(off)}$	Turn-off Delay Time, Inductive Load				200		ns	
t_f	Fall Time, Inductive Load				156		ns	
E_{on}	Turn-on Energy Loss per Pulse				2.64		mJ	
E_{off}	Turn-off Energy Loss per Pulse				1.87		mJ	
$t_{d(on)}$	Turn-on Delay Time, Inductive Load		$I_C=35\text{ A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_G=15\Omega$ $T_{vj}=125\text{ }^\circ\text{C}$		55		ns	
t_r	Rise Time, Inductive Load					60		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load					240		ns
t_f	Fall Time, Inductive Load					240		ns
E_{on}	Turn-on Energy Loss per Pulse				3.22		mJ	
E_{off}	Turn-off Energy Loss per Pulse				3.01		mJ	
R_{thJC}	Thermal resistance, junction to case	per IGBT			0.65	K/W		
$T_{vj\ op}$	Temperature under switching conditions		-40		125	$^\circ\text{C}$		
I_{sc}	SC	$V_{GE}\leq 15\text{ V}, V_{CE}=600\text{ V},$ $t_p\leq 10\mu\text{S}, T_{vj}=125\text{ }^\circ\text{C},$ $V_{CEmax}=V_{CES}-L_{sCE}\cdot di/dt$		160		A		

Maximum Rated Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}=25\text{ }^{\circ}\text{C}$		1200		V
I_F	Continuous DC Forward Current			35		A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ ms}$		70		A
I^2t	I^2t Value	$V_R=0\text{ V}, t_p=10\text{ ms}, T_{vj}=125\text{ }^{\circ}\text{C}$		220		A^2s

Characteristic Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=35\text{ A}, V_{CE}=0\text{ V}, T_{vj}=25\text{ }^{\circ}\text{C}$		1.9	2.5	V
		$I_F=35\text{ A}, V_{CE}=0\text{ V}, T_{vj}=125\text{ }^{\circ}\text{C}$		1.9		V
t_{rr}	Reverse Recovery time	$I_F=35\text{ A}, V_R=600\text{ V}$		170		ns
Q_r	Recovered Charge	$-di/dt=100\text{ A/us}$ $T_{vj}=25\text{ }^{\circ}\text{C},$		0.98		μC
E_{rec}	Reverse Recovery Energy	$V_{GE}=-15\text{ V}$		0.35		mJ
t_{rr}	Reverse Recovery time	$I_F=35\text{ A}, V_R=600\text{ V}$		205		ns
Q_r	Recovered Charge	$-di/dt=100\text{ A/us}$ $T_{vj}=125\text{ }^{\circ}\text{C}$		1.09		μC
E_{rec}	Reverse Recovery Energy	$V_{GE}=-15\text{ V}$		0.36		mJ
R_{thJC}	Thermal resistance, junction to case	per Diode			1.0	K/W
$T_{vj\text{ op}}$	Temperature under switching conditions		-40		125	$^{\circ}\text{C}$

Maximum Rated Values (Diode Rectifier)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25\text{ }^{\circ}\text{C}$		1800		V
I_{FRMSM}	Maximum RMS forward current per chip	$T_c=80\text{ }^{\circ}\text{C}$		70		A
I_{RMSM}	Maximum RMS current at rectifier chip	$T_c=80\text{ }^{\circ}\text{C}$		70		A
I_{FSM}	Surge forward current	$t_p=10\text{ms}$ $T_{vj}=25\text{ }^{\circ}\text{C}$		420		A
I^2t	I^2t -value	$t_p=10\text{ms}$ $T_{vj}=25\text{ }^{\circ}\text{C}$		880		A ² S
I_{FSM}	Surge forward current	$t_p=10\text{ms}$ $T_{vj}=125\text{ }^{\circ}\text{C}$		360		A
I^2t	I^2t -value	$t_p=10\text{ms}$ $T_{vj}=125\text{ }^{\circ}\text{C}$		600		A ² S

Characteristic Values (Diode Rectifier)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward voltage	$T_c=25\text{ }^{\circ}\text{C}$		0.9		V
I_R	Reverse current	$T_{vj}=125\text{ }^{\circ}\text{C}$ $V_R=1800\text{V}$		1.1		mA
R_{thjc}	Thermal resistance junction to case	$T_c=25\text{ }^{\circ}\text{C}$			1.5	K/W
T_{vjop}	Temperature under switching conditions		-40		125	$^{\circ}\text{C}$

Maximum Rated Values (IGBT Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{CES}	Collector-emitter voltage	$T_{vj}=25^{\circ}\text{C}$		1200		V
I_C	Continuous Collector Current	$TC = 80^{\circ}\text{C}, T_{vj} \text{ max} = 150^{\circ}\text{C}$		25		A
I_{CRM}	Peak Collector Current	$I_{CRM}=2I_C$		50		A
V_{GES}	Gate-Emitter Voltage	$T_{vj}=25^{\circ}\text{C}$	-20		20	V

Characteristic Values (IGBT Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=25\text{ A}, V_{GE}=15\text{ V}, T_{vj}=25^{\circ}\text{C}$	1.7	1.85	2.5	V	
		$I_C=25\text{ A}, V_{GE}=15\text{ V}, T_{vj}=125^{\circ}\text{C}$		2.53	2.7	V	
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=5.0\text{ mA}, V_{CE}=V_{GE}, T_{vj}=25^{\circ}\text{C}$	5.2	6.0	6.5	V	
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE}=1200\text{ V}, V_{GE}=0\text{ V}, T_{vj}=25^{\circ}\text{C}$			20	μA	
I_{GES}	Gate-Emitter Leakage Current	$V_{CE}=0\text{ V}, V_{GE}=15\text{ V}, T_{vj}=25^{\circ}\text{C}$			200	nA	
C_{ies}	Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		2.15		nF	
C_{res}	Reverse transfer capacitance		0 V		72.3		pF
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	$I_C=25\text{ A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_{Gon}=20\Omega$ $T_{vj}=25^{\circ}\text{C}$		138		ns	
t_r	Rise Time, Inductive Load			94		ns	
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			220		ns	
t_f	Fall Time, Inductive Load			152		ns	
E_{on}	Turn-on Energy Loss per Pulse				3.53		mJ
E_{off}	Energy Loss per Pulse				1.23		mJ
$t_{d(on)}$	Turn-on Delay Time, Inductive Load		$I_C=25\text{ A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_{Gon}=20\Omega$ $T_{vj}=125^{\circ}\text{C}$		116		ns
t_r	Rise Time, Inductive Load				114		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load				264		ns
t_f	Fall Time, Inductive Load				244		ns
E_{on}	Turn-on Energy Loss per Pulse				4.41		mJ
E_{off}	Turn-off Energy Loss per Pulse				1.81		mJ
R_{thJC}	Thermal resistance, junction to case	per IGBT			1.45	K/W	
T_{vjop}	Temperature under switching conditions		-40		150	$^{\circ}\text{C}$	
I_{sc}	SC	$V_{GE}\leq 15\text{ V}, V_{CE}=600\text{ V}, tp\leq 10\mu\text{S},$ $T_{vj}=150^{\circ}\text{C}, V_{CEmax}=V_{CES}-L_{sCE} \cdot di/dt$		100		A	

Maximum Rated Values (Diode Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}=25\text{ }^{\circ}\text{C}$		1200		V
I_F	Continuous DC Forward Current			15		A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ ms}$		30		A
I^2t	I^2t Value	$V_R=0\text{ V}, t_p=10\text{ ms}, T_{vj}=125\text{ }^{\circ}\text{C}$		100		A^2s

Characteristics (Diode Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
V_F	Forward Voltage	$I_F=15\text{ A}, V_{CE}=0\text{ V}, T_{vj}=25\text{ }^{\circ}\text{C}$		1.9	2.5	V	
		$I_F=15\text{ A}, V_{CE}=0\text{ V}, T_{vj}=125\text{ }^{\circ}\text{C}$		1.90	2.5	V	
t_{rr}	Reverse Recovery time	$I_F=15\text{ A}, V_R=600\text{ V}$ $-di/dt=300\text{ A/us}$		220		ns	
Q_r	Recovered Charge			0.8		μC	
E_{rec}	Reverse Recovery Energy		$T_{vj}=25\text{ }^{\circ}\text{C}$		0.2		mJ
t_{rr}	Reverse Recovery time	$I_F=15\text{ A}, V_R=600\text{ V}$ $-di/dt=300\text{ A/us}$		370		ns	
Q_r	Recovered Charge		$T_{vj}=125\text{ }^{\circ}\text{C}$		1.4		μC
E_{rec}	Reverse Recovery Energy				0.4		mJ
R_{thJC}	Thermal resistance, junction to case	$I_F=15\text{ A}, V_{CE}=0\text{ V}, T_{vj}=25\text{ }^{\circ}\text{C}$			1.75	K/W	
$T_{vj\text{ op}}$	Temperature under switching conditions		-40		125	$^{\circ}\text{C}$	

NTC-Thermistor (Characteristic Values)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R ₂₅	Rated resistance	T _c =25 °C		5		KΩ
ΔR/R	Deviation of R100	T _c =100 °C	-5		5	%
P ₂₅	Power dissipation	T _c =25 °C		20		mW
B _{25/50}	B-value	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15K))]$		3380		K
B _{25/100}	B-value	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15K))]$		3450		K

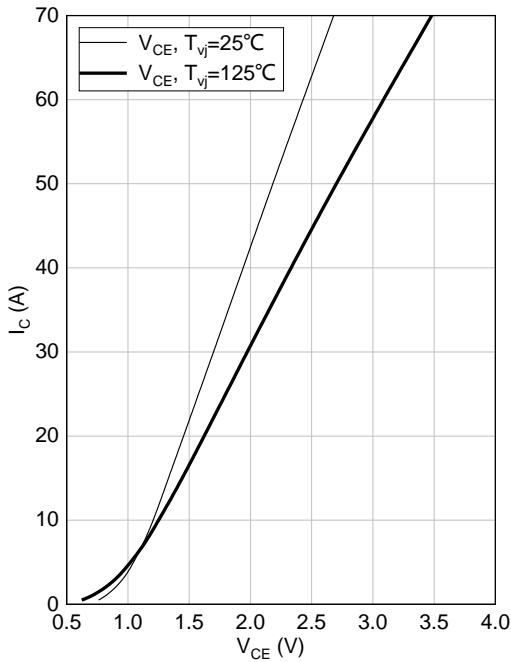
Module Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{isol}	Isolation voltage	t=1min,f=50Hz	2500			V
T _{stg}	Storage Temperature		-40		125	°C
F	Mounting Force per Clamp		40		80	N
G	Weight of Module			40		g

Output characteristic of IGBT, Inverter (typical)

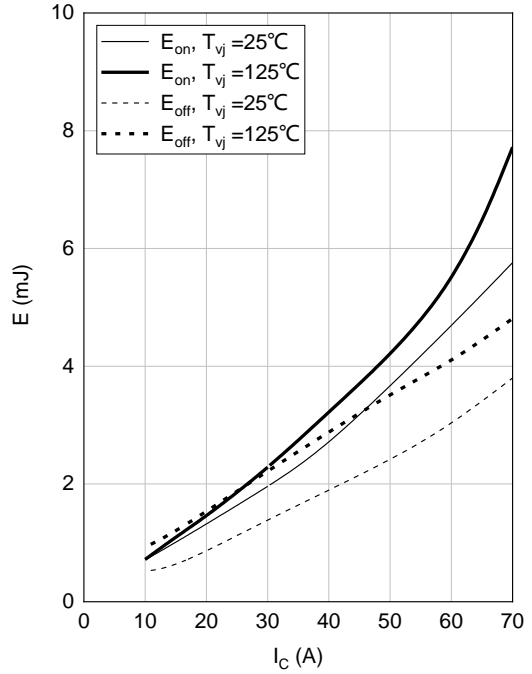
$$I_c = f(V_{CE})$$

$$V_{GE} = 15V$$


Switching time of IGBT, Inverter (typical)

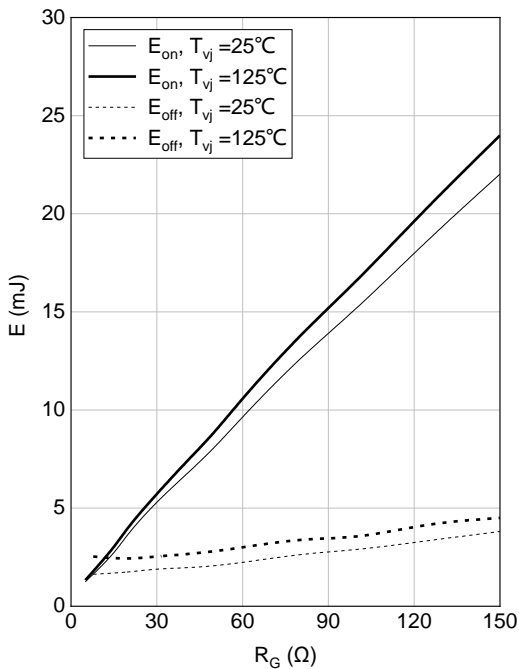
$$E_{on} = f(I_c), E_{off} = f(I_c)$$

$$V_{GE} = \pm 15V, R_G = 15\Omega, V_{CE} = 600V$$


Switching losses of IGBT, Inverter (typical)

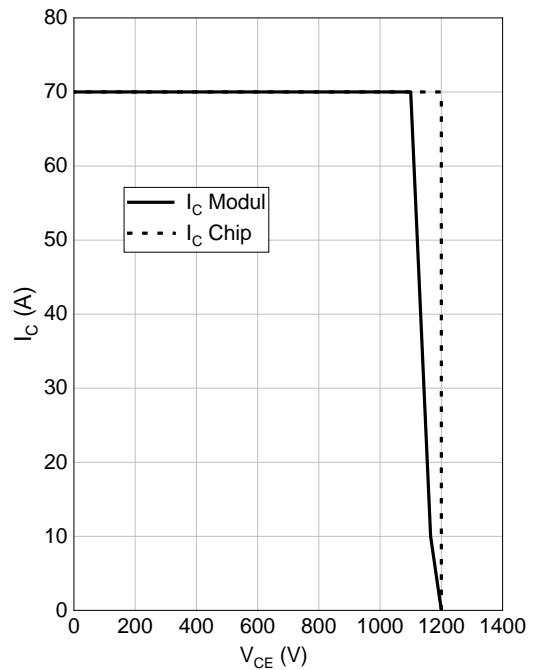
$$E_{on} = f(R_G), E_{off} = f(R_G)$$

$$V_{GE} = \pm 15V, I_c = 35A, V_{CE} = 600V$$

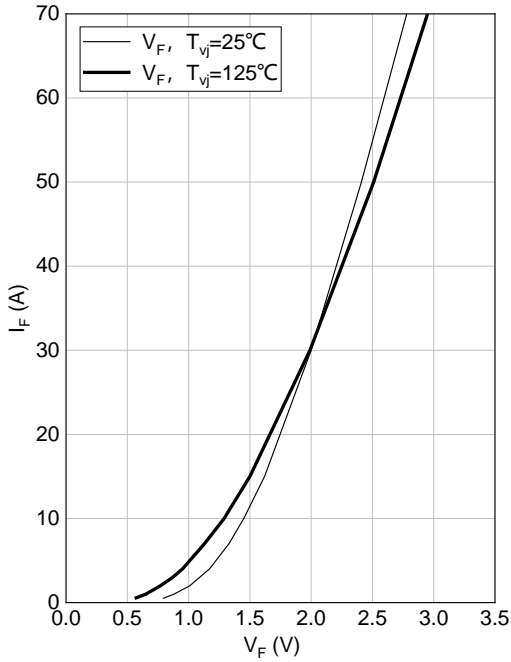

RBSOA IGBT, Inverter (typical)

$$I_c = f(V_{CE})$$

$$V_{GE} = \pm 15V, R_{Goff} = 15\Omega, T_{vj} = 125^\circ C$$

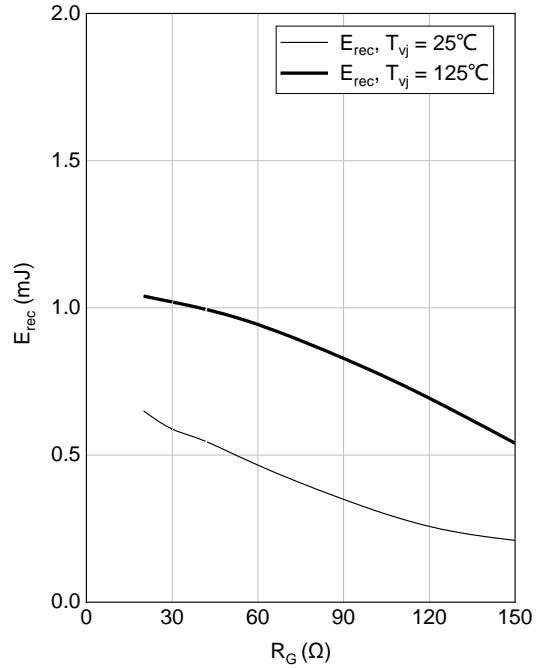


Forward characteristic of Diode, Inverter (typical)
 $I_F = f(V_F)$



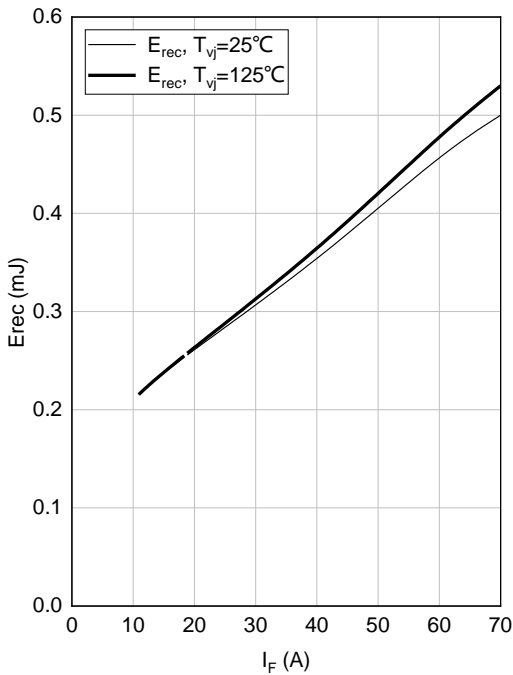
Switching losses of Diode, Inverter (typical)

$E_{rec} = f(R_G)$,
 $I_F = 35A, V_{CE} = 600V$



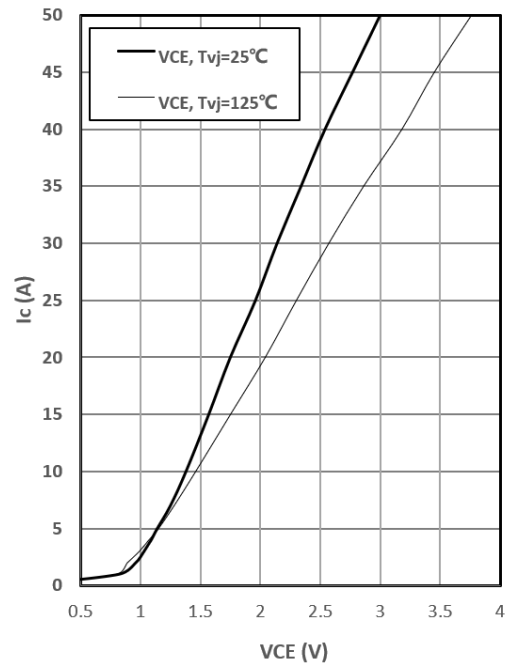
Switching losses of Diode, Inverter (typical)

$E_{rec} = f(I_F)$,
 $R_{Gon} = 15\Omega, V_{CE} = 600V$



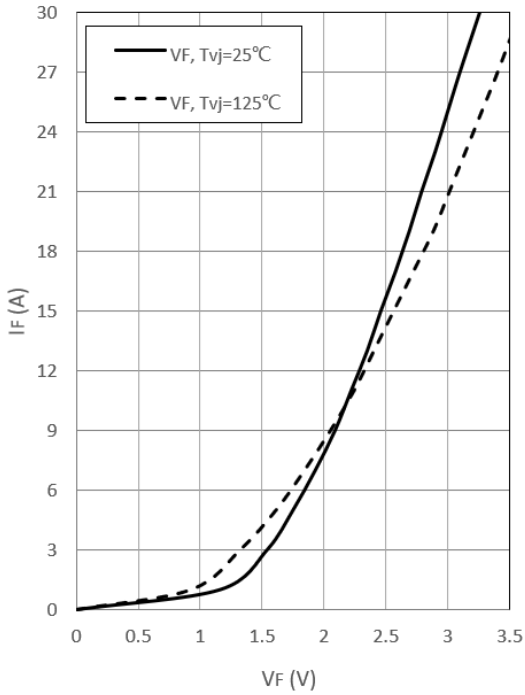
Output characteristic of IGBT, Brake-Chopper, (typical)

$I_c = f(V_{CE})$
 $V_{GE} = 15V$



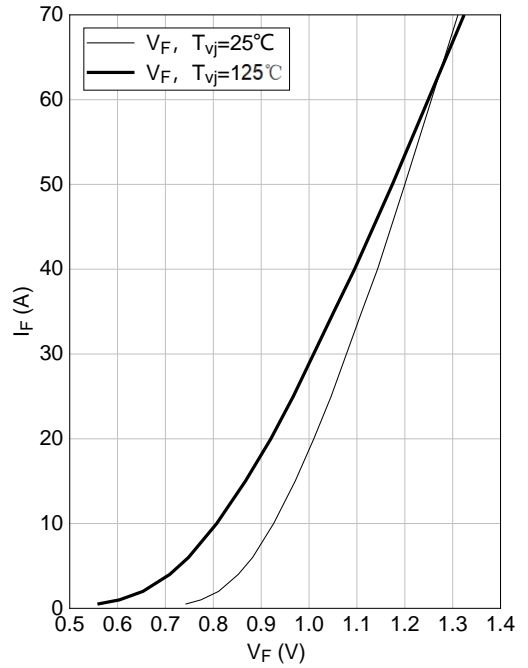
Forward characteristic of Diode, Brake-Chopper (typical)

$$I_F = f(V_F)$$



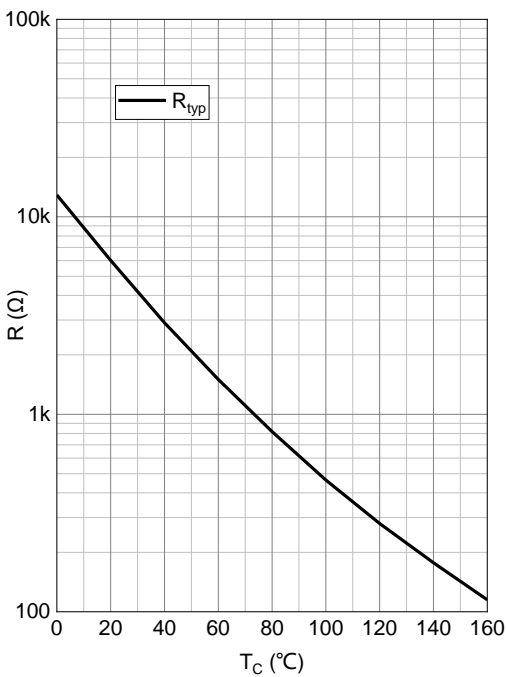
Forward characteristic of Diode, Rectifier (typical)

$$I_F = f(V_F)$$

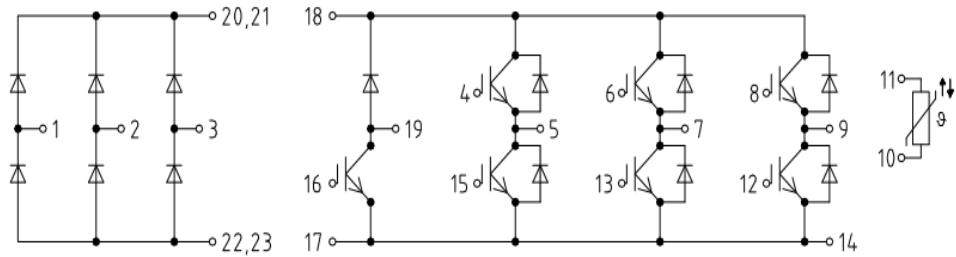


NTC-thermistor-temperature characteristic (typical)

$$R = f(T_{NTC})$$

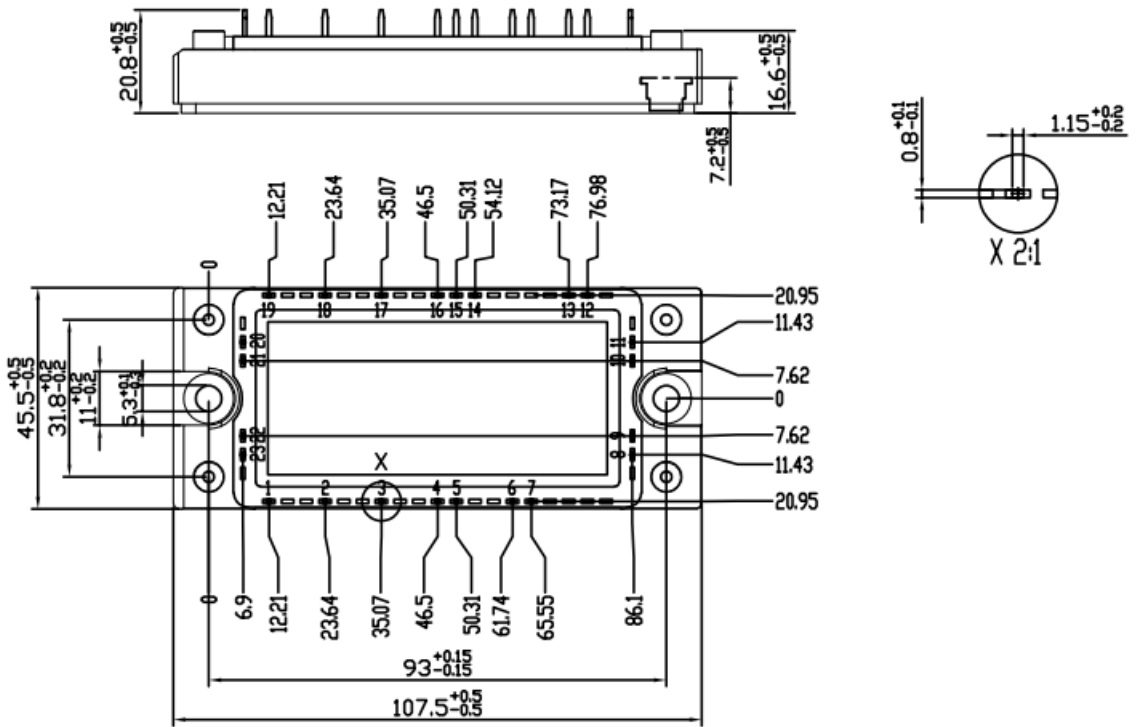


Circuit Diagram



Package Dimensions

(Dimensions in Millimeters)



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